Implications of Ga Promotion and Metal-Oxide Interface from Tailored PtGa Propane Dehydrogenation Catalysts Supported on Carbon

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Experimental Details

General Procedures & Considerations: All operations were performed in a M. Braun glove box under an Argon atmosphere or using high vacuum and standard Schlenk techniques. Pentane and benzene were purged with argon for 30 minutes and pre-dried using a MB SPS 800 solvent purification system, where columns were packed with activated alumina. Deuterated benzene was vacuum distilled from purple Na⁰/benzophenone. All solvents were stored over 4 Å molecular sieves after being placed in the glove box. Molecular sieves as well as celite were activated at 350 °C under high vacuum overnight. Titration of the carbon supports was performed using [Mg(Bn)₂(THF)₂] and Ferrocene which were purified via sublimation prior to use. $[Mg(Bn)_2(THF)_2]^1$, $[Pt(COD)(OSi(O^{t}Bu_{3})_{3})_{2}]^{2},$ allyl-(N-N'-diisopropyl)acetamidinate [Ga(OSi(O^tBu₃)₃)₃(THF)]³, $[Ga(Mes)_3]^4$, platinum ([Pt(AMD)])⁵ and were prepared according to literature procedures.

Mesoporous carbon (>99.95% trace metal basis, Product Nr. 699624) was bought form Sigma-Aldrich. All other reagents were bought from commercial sources and used as received. Mikroanalytisches Labor Pascher located in Remagen, Germany, performed the elemental analysis.

Carbon Functionalisation

Mesoporous Carbon (6 g) was refluxed at 125 °C in 150 mL concentrated HNO₃ in a 250 mL round bottom flask equipped with a reflux condenser for 12 hours, as previously reported⁶. The solid was then filtered off using a glass filter and washed with large portions of water (3 x 100mL of milliQ water) and ethanol (2 x 100 mL), followed by drying under high vacuum (10⁻⁵ mbars) at 200 °C for 12 hours.

OH Titration

A solution of $[Mg(Bn)_2(THF)_2]$ (16.8 mg, 0.08 mmol) in C₆D₆ was added slowly to a suspension of mesoporous carbon (52.5 mg) while stirring. The resulting mixture was stirred for 24 hours, after which a ferrocene (6.4 mg, 0.03 mmol) solution was added and an NMR spectrum measured (recycle delay d1 = 60s).

Synthesis of Ptx_Siz/Cgrafted and Ptx/Cgrafted

Pt_{0.68}_Si_{0.1}/C_{gratted} from [Pt(OSi(O^tBu)₃)₂(COD)] precursor:

A solution of $[Pt(OSi(O^tBu)_3)_2(COD)]$ (103.4 mg, 0.125 mmol) in benzene was added slowly to a suspension of mesoporous carbon (750.3 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

Pt_{0.60}/C_{grafted} from [Pt(AMD)] precursor:

A solution of [Pt(AMD)] (52.9 mg, 0.140 mmol) in benzene was added slowly to a suspension of mesoporous carbon (844.0 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

Synthesis of Ptx_Siz/CH2 and Ptx/CH2

Pt_{0.68}_Si_{0.1}/C_{H2} from Pt_{0.68}_Si_{0.1}/C_{grafted} precursor:

 $Pt_{0.68}$ _Si_{0.1}/C_{grafted} was subjected to a hydrogen flow treatment at 600 °C (300 °C/h ramp) and 1 bar of hydrogen for 12 hours, followed by evacuation under high vacuum and storage in a glovebox to give carbon supported platinum nanoparticles ($Pt_{0.68}$ _Si_{0.1}/C_{H2}).

Pt_{0.60}/C_{H2} from Pt_{0.60}/C_{grafted} precursor:

 $Pt_{0.60}/C_{grafted}$ was subjected to a hydrogen flow treatment at 600 °C (300 °C/h ramp) and 1 bar of hydrogen for 12 hours, followed by evacuation under high vacuum and storage in a glovebox to give carbon supported platinum nanoparticles ($Pt_{0.60}/C_{H2}$).

Synthesis of Gay_Siz/Cgrafted and Gay/Cgrafted

Ga_{1.00}/C_{grafted} from [Ga(OSi(O^tBu)₃)₃(THF)] precursor:

A solution of $[Ga(OSi(O^tBu)_3)_3(THF)]$ (118.7 mg, 0.13 mmol) in benzene was added slowly to a suspension of mesoporous carbon (748.9 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

Ga_{0.10}/C_{grafted} from [Ga(Mes)₃] precursor:

A solution of [Ga(Mes)₃] (91.9 mg, 0.22 mmol) in benzene was added slowly to a suspension of mesoporous carbon (1265.0 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

Synthesis of PtxGay_Siz/Cgrafted and PtxGay/Cgrafted

Pt_xGa_y_Si_z/C_{grafted} from [Pt(OSi(O^tBu)₃)₂(COD)] precursor:

A solution of $[Pt(OSi(O^tBu)_3)_2(COD)]$ (47.4 mg, 0.06 mmol) in benzene was added slowly to a suspension of Ga_{1.00}_Si_z/C_{grafted} (340.2 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

PtxGay/Cgratted from [Pt(AMD)] precursor:

A solution of [Pt(AMD)] (42.7 mg, 0.11 mmol) in benzene was added slowly to a suspension of $Ga_{0.10}/C_{grafted}$ (674.2 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum.

Synthesis of Pt_xGay_Si₂/C_{H2} and Pt_xGay/C_{H2}

The corresponding $Pt_xGa_y_Si_z/C_{grafted}$ and $Pt_xGa_y/C_{grafted}$ materials were subjected to a hydrogen flow treatment at 600 °C (300 °C/h ramp) and 1 bar of hydrogen for 12 hours, followed by evacuation under high vacuum and storage in a glovebox.

Synthesis of low loading Pt_xGa_y_Si_z/C_{H2}

A solution of $[Ga(OSi(O^tBu)_3)_3(THF)]$ (11.6 mg, 0.12 mmol) in benzene was added slowly to a suspension of mesoporous carbon (750.0 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum, giving Ga_{0.10}Si_{0.31}/C_{grafted}.

Then, a solution of $[Pt(OSi(O^tBu)_3)_2(COD)]$ (6.1 mg, 0.007 mmol) in benzene was added slowly to the suspension of $Ga_{0.10}Si_{0.31}/C_{grafted}$ (340.2 mg) while stirring. The resulting mixture was stirred for 24 hours, then the carbon was filtered off, washed twice with benzene (5 mL) and followed by pentane (5 mL) and drying in high vacuum, giving $Pt_{0.15}Ga_{0.10}Si_{0.31}/C_{grafted}$.

 $Pt_{0.15}Ga_{0.10}$ _Si_{0.31}/C_{grafted} was then subjected to a hydrogen flow treatment at 600 °C (300 °C/h ramp) and 1 bar of hydrogen for 12 hours, followed by evacuation under high vacuum to give $Pt_{0.15}Ga_{0.10}$ _Si_{0.31}/C_{H2}, which was stored in a glovebox.

XPS Studies

XPS analysis was performed using the SIGMA II instrument equipped with an AI/Mg twin anode. The vacuum in the chamber was around $5x10^{-8}$ mbar during measurements. The analyses were carried out with a Mg-Ka source (energy = 1286.6 eV, 0.1 eV step size) in LAXPS mode with a pass energy of 16 eV. The curve-fitting was performed with Shirley background and line shape GL(30). C1s was used for referencing at 284.8 eV. RSFs were used to allow for semi-quantitative analysis of surface species.



Figure S1. C 1s XPS spectrum of untreated mesoporous carbon as received from Sigma Aldrich.



Figure S2. C 1s (top) and O 1s (bottom) XPS spectra of HNO₃-treated mesoporous carbon.

N₂ Adsorption Isotherm

Nitrogen adsorption isotherms were recorded on a Bel-Mini apparatus (BEL Japan, Inc.) at 77 K. Approximately 100 mg of the sample were loaded into the cells. Prior to the adsorption measurement, the samples coming from the glovebox, were evacuated under vacuum (ca. 10^{-3} mbar) at R.T. for 1 h. Data were fitted according to a BET theory to obtain the specific surface area.



Figure S3. N₂ Adsorption isotherms of C before (*left*) and after (*right*) HNO₃ oxidative treatment.

Catalytic Propane Dehydrogenation Studies

Catalytic tests were performed utilizing a quartz flow reactor designed in our laboratories and a heating/flow setup designed and produced by Micromeritics Instrument Cooperation (PID Eng & Tech). Catalyst samples were loaded into quartz tubular reactor in an Ar filled glovebox. Prior to exposing the catalyst to flow conditions, a bypass was purged for 20 min with Ar (40 mL/min). The samples were then heated to 550 °C utilizing a tubular furnace under a flow of Ar (40 mL/min) and the temperature was maintained until fully stabilized. The propane containing gas mixture was subsequently mixed and purged through a bypass for 20 min at the desired flow rate for the reaction prior to contact with the catalyst. Reaction temperatures were maintained utilizing a quartz encased thermocouple maintained in contact with the catalyst dispersed in SiC to yield a total weight of ~2.5 g. The output gas composition was analysed automatically by a GC with a flame ionization detector (FID) which was programmed to sample the gas stream every 9 minutes throughout the time of reaction. Gases were purified by passing through a column with molecular sieves and Q5 catalyst prior to introduction to the flow reactor. Propane conversion, selectivity and the carbon balance were calculated according to following equations:

Conversion:

$$X_{C_3H_8} = 1 - \frac{n_{C_3H_8,out}}{n_{C_3H_8,out} + n_{C_3H_6,out} + n_{C_2H_6,out}/1.5 + n_{C_2H_4,out}/1.5 + n_{CH_4,out}/3}$$

Selectivity:

$$S = \frac{n_{i,out} * \#Carbonatoms/3}{n_{C_3H_8,out} + n_{C_3H_6,out} + n_{C_2H_6,out} * 2/3 + n_{C_2H_4,out} * 2/3 + n_{CH_4,out}/3}$$

Carbon Balance:

$$Carbon \ Balance = \frac{n_{C_{3}H_{8},in}}{n_{C_{3}H_{8},out} + n_{C_{3}H_{6},out} + n_{C_{2}H_{6},out} + n_{C_{2}H_{4},out} + n_{CH_{4},out}}$$

Deactivation constant:

$$k_D = \frac{\ln\left(\frac{1 - conv_{end}}{conv_{end}}\right) - \ln\left(\frac{1 - conv_{start}}{conv_{start}}\right)}{t}$$

Standard PDH conditions: 550 °C, 50 ml/min, 1 bar, 1:4 C₃H₈/Ar for varying times.

The catalytic activity of $Pt_{0.68}$ _Si_0.1/C_{H2}, $Pt_{0.60}$ /C_{H2}, $Pt_{0.89}Ga_{1.00}$ _Si_1.64/C_{H2} and $Pt_{0.26}Ga_{0.10}$ /C_{H2} in the dehydrogenation of propane are summarized in Figure S32. For a typical catalytic test, varying amounts of catalyst (61.9 mg $Pt_{0.68}$ _Si_0.1/C_{H2}, 51.8 mg $Pt_{0.89}Ga_{1.00}$ _Si_1.64/C_{H2},124.1 mg $Pt_{0.60}$ /C_{H2} or 118.4 mg $Pt_{0.26}Ga_{0.10}$ /C_{H2}) were used while maintaining identical gas composition and flow rate with a flow of 50 mL/min with 1:4 C₃H₈/Ar (any ratios of gases given is in volume ratio). In all cases conversions below equilibrium are achieved. The flow rates, temperatures and pressures used during the different catalytic tests are summarized in the following. Standard PDH conditions: 550 °C, 50 ml/min, 1 bar, 1:4 C₃H₈/Ar (v:v) for varying times.



Formation Rates vs. Time

Figure S4. Formation rates as a function of time on stream (TOS) of



Figure S5. Product selectivities as a function of time on stream (TOS) of $Pt_{0.68}$ _Si_{0.1}/C_{H2} and $Pt_{0.60}$ /C_{H2} catalysts.

Selectivity vs. Time



XAS Studies

XAS measurements were carried out at the Ga K-edge and Pt L₃-edge at the SuperXAS beamline at SLS (PSI, Villigen, Switzerland). The storage ring was operated at 2.4 GeV in topup mode with a ring current of around 400 mA. The incident photon beam provided by a 2.9 T superbend magnet was selected by a Si(111) quick-EXAFS monochromator and the rejection of higher harmonics and focusing were achieved by a rhodium-coated collimating mirror at 2.5 mrad and a rhodium-coated torroidal mirror at 2.5 mrad. The beam size on the sample was 100 x 100 µm. During measurements, the monochromator was rotating with 1 Hz frequency in 2 deg angular range and X-ray absorption spectra were collected in transmission mode using ionization chambers specially developed for quick data collection with 1 MHz frequency.⁷ The spectra were collected for 3 min and averaged. The beamline energy was calibrated with the Pt reference foil to the Pt L₃-edge position at 11564.0 eV. To avoid contact with air, all samples were sealed in a glovebox. For ex situ samples, pressed pellets (with optimized thickness for transmission detection) were placed in two aluminized plastic bags (Polyaniline (15 µm), polyethylene (15 μm), AI (12 μm), polyethylene (75 μm) from Gruber-Folien GmbH & Co. KG, Straubing, Germany) using an impulse sealer inside a glovebox; one sealing layer was removed immediately before the measurements. For in-situ measurements, catalyst beds of appropriate mass were supported with quartz wool in 3 mm quartz capillaries. Gas flow and composition were controlled using Bronkhorst mass flow controllers and a back-pressure regulator. Flow rates during H₂ reduction were maintained at 10 ml/min with a pressure of 1 atmosphere. Ar and H_2 were purified by passing through a column with molecular sieves and Q5 catalyst prior to introduction to the XAS guartz cell. Data processing was done by standard procedures using the ProXASGui software developed at the SuperXAS beamline, PSI, Villigen. The program package Demeter was used for data analysis.8



Figure S8. Ex situ Pt L₃-Edge XANES spectra of all prepared Pt catalysts and Pt foil reference.



Figure S9. *Ex situ* Pt L₃-Edge XANES spectra of monometallic Pt catalysts and Pt foil reference.



Figure S10. *Ex situ* Ga K-Edge XANES spectra of $Pt_{0.89}Ga_{1.00}$ _Si_{1.64}/C_{grafted}, $Pt_{0.89}Ga_{1.00}$ _Si_{1.64}/C_{H2}, $Pt_{0.26}Ga_{0.10}$ /C_{grafted}, $Pt_{0.26}Ga_{0.10}$ /C_{H2} catalysts and Ga metal reference.



Figure S11. In situ Pt L₃-Edge XANES spectra of $Pt_{0.68}$ _Si_{0.1}/C_{grafted} under a flow of 1 barg of H₂ (10 mL/min) and a temperature range of 25 °C to 600 °C.



Figure S12. In situ Pt L₃-Edge XANES spectra of $Pt_{0.60}/C_{grafted}$ under a flow of 1 barg of H₂ flow (10 mL/min) and a temperature range of 25 °C to 600 °C.

Ex Situ (S)TEM & STEM-EDS Studies

TEM and STEM measurements were recorded on a double C_S corrected JEOL JEM-ARM300F Grand ARM "Vortex" (scanning) transmission electron microscope operated at accelerating voltages of 200 or 300 kV. Ga containing samples were dry casted as solid onto 200 mesh 5 nm thick C QUANTIFOIL copper grids in an Argon glovebox and mounted on a vacuum transfer holder (GATAN, Mel-Build).

Pt_{0.68}_Si_{0.1}/C_{grafted}



Figure S13. HAADF- (*left*) and ABF-STEM (*right*) images of Pt_{0.68}_Si_{0.1}/C_{grafted}.

Pt_{0.68}_Si_{0.1}/C_{H2}

Fresh Catalyst



Figure S14. HAADF-STEM image of $Pt_{0.68}$ _Si_0.1/C_{H2} (*left*) and particle size distribution (*right*).



Figure S15. ABF (*left*) and HAADF-STEM (*right*) images of Pt_{0.68}_Si_{0.1}/C_{H2}.



Figure S16. HAADF-STEM EDS maps and spectrum of $Pt_{0.68}$ _Si_{0.1}/C_{H2}.

Element	Energy	Mass%	Counts	Atom%
	(keV)			
CK	-	n.q.	n.q.	n.q.
ОК	0.525	45.72	19368	78.74
Si K	1.739	16.19	11567	15.88
Pt M	2.048	38.10	7142	5.38

Table S1. Quantification of STEM-EDS spectrum of $Pt_{0.68}_Si_{0.1}/C_{H2}.$

Spent Catalyst



Figure S17. HAADF-STEM image of $Pt_{0.68}$ Si_{0.1}/C_{H2} after catalysis (*left*) and particle size distribution (*right*).



Figure S18. ABF (*left*) and HAADF-STEM (*right*) images of Pt_{0.68}_Si_{0.1}/C_{H2} after catalysis.

Pt_{0.60}/C_{H2}

Fresh Catalyst



Figure S19. HAADF-STEM image of $Pt_{0.60}/C_{H2}$ (*left*) and particle size distribution (*right*).



Figure S20. ABF (*bottom, right*) & HAADF-STEM (*left*) and TEM (*top, right*) images of Pt_{0.60}/C_{H2}.



Figure S21. HAADF-STEM EDS maps and spectrum of $Pt_{0.60}/C_{\text{H2}}.$

able 52. Quantification of STEM-EDS spectrum of $F_{10.60}/GH_2$.						
	Element	Energy	Mass%	Counts	Atom%	
		(keV)				
	СК	0.277	98.32	300487	99.02	-
	ОК	0.525	1.26	7560	0.96	
	Si L	1.739	n.d.	n.d.	n.d.	
	Pt M	2.048	0.41	1425	0.03	

Table S2. Quantification of STEM-EDS spectrum of Pt_{0.60}/C_{H2}.

Spent Catalyst



Figure S22. HAADF- and ABF STEM image of $Pt_{0.60}/C_{H2}$ after catalysis and particle size distribution.

Pt0.89Ga1.00_Si1.64/CH2

Fresh Catalyst



Figure S23. HAADF-STEM image of $Pt_{0.89}Ga_{1.00}$ _Si_{1.64}/C_{H2} (*left*) and particle size distribution (*right*).



Figure S24. ABF (*top, left*) and HAADF-STEM (*rest*) images of Pt_{0.89}Ga_{1.00}_Si_{1.64}/C_{H2}.



Figure S25. HAADF-STEM EDS maps and spectrum of $Pt_{0.89}Ga_{1.00}$ _Si_{1.64}/C_{H2}.

Element	Energy (keV)	Mass%	Counts	Atom%
СК	0.277	94.28	48862	97.94
ОК	0.525	1.75	2180	1.37
Si K	1.739	0.32	745	0.14
Pt M	2.048	0.87	2896	0.50
Ga L	1.098	2.78	530	0.06

Table S3. Quantification of STEM-EDS spectrum of Pt_{0.89}Ga_{1.00}_Si_{1.64}/C_{H2}.

Spent Catalyst



Figure S26. HAADF-STEM image of Pt_{0.89}Ga_{1.00}_Si_{1.64}/C_{H2} after catalysis (*left*) and particle size distribution (*right*).



Figure S27. ABF (*left*) & HAADF-STEM (*right*) images of Pt_{0.89}Ga_{1.00}_Si_{1.64}/C_{H2} after catalysis.



Element	Energy	Mass%	Counts	Atom%
	(keV)			
	0.077	0.70	440	6.06
CK	0.277	2.73	412	6.96
ОК	0.525	31.86	10956	60.90
ÖR	0.020	01.00	10950	00.00
Si K	1.739	20.60	11949	22.44
Pt M	2.048	35.32	5375	5.54
Ga L	1.098	9.50	1189	4.17

Table S4. Quantification of STEM-EDS spectrum of $Pt_{0.89}Ga_{1.00}Si_{1.64}/C_{H2}$ after catalysis.

Pt0.26Ga0.10/CH2



Figure S29. HAADF-STEM image (*left*) of Pt_{0.26}Ga_{0.10}/C_{H2}.and particle size distribution (*right*).



Figure S30. ABF (*left*) & HAADF-STEM (*right*) images of Pt_{0.26}Ga_{0.10}/C_{H2}.



Figure S31. HAADF-STEM EDS maps and spectrum of $Pt_{0.26}Ga_{0.10}/C_{H2}$.

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Element	Energy	Mass%	Counts	Atom%	
	(keV)				
 СК	0.277	98.83	845358	99.59	_
ОК	0.525	0.43	8833	0.33	
Si K	1.739	0.01	351	0.00	
Pt M	2.048	0.38	2797	0.06	
Ga L	1.098	0.35	3836	0.02	

Table S5. Quantification of STEM-EDS spectrum of Pt_{0.26}Ga_{0.10}/C_{H2}.

Spent Catalyst



Figure S32. HAADF- and ABF STEM image of $Pt_{0.26}Ga_{0.10}/C_{H2}$ after catalysis and particle size distribution.

4D STEM Measurements

4D STEM measurements were performed on a JEOL JEM-F200 STEM microscope. The convergence-beam electron diffraction pattern at each probe position was recorded using a 4K Gatan RiO CMOS camera, operated at 160 frames per second. The camera acquisition and probe scanning were synchronized using a Gatan Digiscan3. Diffraction patterns were obtained over an area of 128×128 pixels (pixel size: 0.024nmx0.024nm), with an acquisition time of 7ms and recorded in 1k resolution binned by 2. Ga containing samples were dry casted as solid onto 200 mesh 5 nm thick C QUANTIFOIL copper grids in an Argon glovebox and mounted on a vacuum transfer holder (GATAN, Mel-Build). For 4D STEM measurements, 200 mesh C QUANTIFOIL copper grids were used. All other samples were suspended in methanol by ultra-sonification and drop-casted onto 200 mesh 5 nm C QUANTIFOIL copper grids.



Figure S33. 4D STEM spectrum Image (*left*), diffraction pattern (*middle*) and signal (*right*) from selected diffraction disk of middle image of $Pt_{0.60}/C_{H2}$.



Figure S34. 4D STEM spectrum Image (*left*), diffraction pattern (*middle*) and signal (*right*) from selected diffraction disk of middle image of $Pt_{0.68}$ _Si_0.1/C_{H2}.



Figure S35. 4D STEM spectrum Image (*left*), diffraction pattern (*middle*) and signal (*right*) from selected diffraction disk of middle image of $Pt_{0.89}Ga_{1.00}$ _Si_{1.64}/C_{H2}.



Figure S36. 4D STEM spectrum Image (*left*), diffraction pattern (*middle*) and signal (*right*) from selected diffraction disk of middle image of $Pt_{0.26}Ga_{0.10}/C_{H2}$.

References

- 1. J. J. Sandoval, P. Palma, E. Álvarez, J. Cámpora and A. Rodríguez-Delgado, *Organometallics* **2016**, 35, 3197-3204.
- 2. D. A. Ruddy, J. Jarupatrakorn, R. M. Rioux, J. T. Miller, M. J. McMurdo, J. L. McBee, K. A. Tupper and T. D. Tilley, *Chem. Mater.* **2008**, 20, 6517-6527.
- 3. K. Searles, G. Siddiqi, O. V. Safonova and C. Copéret, *Chem. Sci.* **2017**, 8, 2661-2666.
- 4. O. T. Beachley, Jr., M. R. Churchill, J. C. Pazik and J. W. Ziller, *Organometallics* **1986**, 5, 1814-1817.
- 5. C. Ehinger, X. Zhou, M. Candrian, S. R. Docherty, S. Pollitt and C. Copéret, *JACS Au* **2023**, *in press*, DOI: 10.1021/jacsau.3c00334.
- 6. C. K. Mavrokefalos, N. Kaeffer, H.-J. Liu, F. Krumeich and C. Copéret, *ChemCatChem* **2020**, 12, 305-313.
- 7. O. Müller, J. Stötzel, D. Lützenkirchen-Hecht and R. Frahm, *Journal of Physics: Conference Series* **2013**, 425, 092010.
- 8. B. Ravel and M. Newville, *Journal of Synchrotron Radiation* **2005**, 12, 537-541.